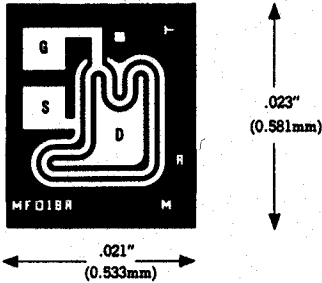


CHIP NUMBER

FMN1.1



Die Size: 21 x 23 (mils)  
0.530 x 0.534(mils)  
Pad Size: 4 x 4 (mils)  
BODY-SUBSTRATE

**CONTACT METALLIZATION**

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

**ASSEMBLY RECOMMENDATIONS**

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

**TYPICAL ELECTRICAL CHARACTERISTICS**

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVDSS	25	30		V	$I_D = +10 \mu A, V_{GS} = 0, V_{BS} = 0$
IDSS		10	500	pA	$V_{DS} = +15V, V_{GS} = 0, V_{BS} = 0$
$g_{fs}$	1000	2500	4000	$\mu mho$	$V_{DS} = +15V, I_D = 2mA, f = 1KHz$
IGSS		0.1	10	pA	$V_{GS} = \pm 40V, V_{DS} = 0$
$r_{DS(on)}$		60	195	$\Omega$	$V_{DS} = 20V, I_D = 10mA, V_{BS} = 0$
VGS(Th)	+ .5	+ 1.5	+ 5.0	V	$V_{DS} = +15V, I_D = +10mA, V_{BS} = 0$
$C_{rss}$		1.0	1.3	pF	$V_{DS} = +15V, I_D = +10mA, f = 1MHz$
$C_{iss}$		4.5	5	pF	$V_{DS} = +15V, I_D = 10mA, f = 1KHz$

TYPICAL DEVICE TYPES: 3N169, 3N170, 3N171

CHIP TYPE FMN1.1

